## SOI WAFERS - SPECIFICATION SOI-380-1-10

**Bonded Wafer**
- Diameter: \(100 \pm 0.5\text{mm}\)
- Thickness: \(391 \pm 10\mu\text{m}\)
- Primary Flat Orientation: \{110\} \(\pm 1.0^\circ\)
- Primary Flat Length: \(32.5 \pm 2.5\text{mm}\)
- Secondary Flat Location: No secondary flat
- Edge Profile: Rounded edge
- Laser Marking: On backside of wafers according to PO
- Back Surface Quality: Polished
- Front Surface Quality: No scratches, haze, edge chips, orange peel, defects

**Handle Wafer**
- Doping type: P
- Dopant: Boron
- Crystal Orientation: \{100\}
- Off-Orientation: \(0.0 \pm 0.5^\circ\)
- Resistivity: \(1 – 10\) Ohmcm
- Thickness: \(380 \pm 10\mu\text{m}\)

**Buried Oxide**
- Oxide Thickness: \(1.00 \pm 0.05\mu\text{m}\)

**Device Wafer**
- Doping type: P
- Dopant: Boron
- Crystal Orientation: \{100\}
- Off-Orientation: \(0.0 \pm 0.5^\circ\)
- Resistivity: \(1 – 10\) Ohmcm
- Thickness: \(10.0 \pm 0.7\mu\text{m}\)
- Edge non-SOI area: \(< 1.2\text{mm} (preferably 0mm if not affecting quality)\)